2SC4292

NPN triple diffused planar silicon transistor

Package
- TO-3PB

Use
- Very high-definition color display, horizontal deflection output

Features
- High speed (t_f=300ns typ.)
- High breakdown voltage (V_{CBO}=1500V)
- High reliability (adoption of HVP process)
- Adoption of MBIT process
- On-chip damper diode

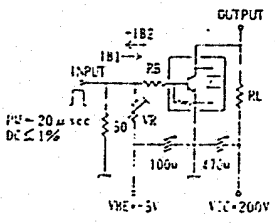
Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current	I_C	6	A
Peak Collector Current	icp	16	A
Collector Dissipation	P_C	100	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

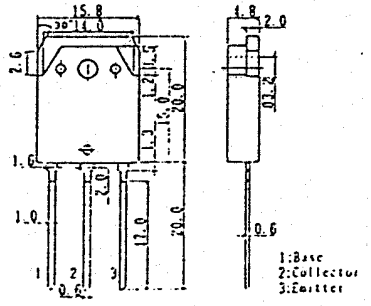
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CES}	V_{CE}=1500V			1.0	mA
Collector Cutoff Current	I_{CBO}	V_{CB}=800V			10	uA
Collector Sustain Voltage	V_{CEO}(sus)	I_C=100mA,I_B=0	800			V
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V	40		130	mA
Collector to Emitter Saturation Voltage	V_{CE}(sat)	I_C=5A,I_B=1.2A			5	V
Base to Emitter Saturation Voltage	V_{BE}(sat)	I_C=5A,I_B=1.2A			1.5	V
DC Current Gain	h_{FE}(1)	V_{CE}=5V,I_C=1.0A	8			
	h_{FE}(2)	V_{CE}=5V,I_C=5A	4		6	
Diode Forward Voltage	V_F	I_{EC}=6A			2.0	V
Storage Time	tstg	I_C=5A,I_{B1}=1A,I_{B2}=-2A			3.0	us
Fall Time	tf	I_C=5A,I_{B1}=1A,I_{B2}=-2A			0.3	us

Switching Time Test Circuit



Case Outline (unit:mm)



Specifications and information herein are subject to change without notice.

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